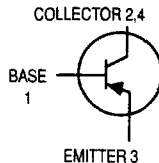


High Voltage Transistor

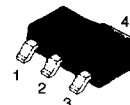
PNP Silicon



PZTA96T1

Motorola Preferred Device

SOT-223 PACKAGE
PNP SILICON
HIGH VOLTAGE TRANSISTOR
SURFACE MOUNT



CASE 318E-04, STYLE 1
TO-261AA

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-450	Vdc
Collector-Base Voltage	V_{CBO}	-450	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current	I_C	-500	mAdc
Total Power Dissipation up to $T_A = 25^\circ\text{C}^{(1)}$	P_D	1.5	Watts
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Junction Temperature	T_J	150	$^\circ\text{C}$

DEVICE MARKING

ZTA96

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance from Junction to Ambient ⁽¹⁾	$R_{\theta JA}$	83.3	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = -1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	-450	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = -100$ μ Adc, $I_E = 0$)	$V_{(BR)CBO}$	-450	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = -10$ μ Adc, $I_C = 0$)	$V_{(BR)EBO}$	-5.0	—	Vdc
Collector-Base Cutoff Current ($V_{CB} = -400$ Vdc, $I_E = 0$)	I_{CBO}	—	-0.1	μ Adc
Emitter-Base Cutoff Current ($V_{BE} = -4.0$ Vdc, $I_C = 0$)	I_{EBO}	—	-0.1	μ Adc

ON CHARACTERISTICS

DC Current Gain ⁽²⁾ ($I_C = -10$ mAdc, $V_{CE} = -10$ Vdc)	h_{FE}	50	150	—
Saturation Voltages ($I_C = -20$ mAdc, $I_B = -2.0$ mAdc) ($I_C = -20$ mAdc, $I_B = -2.0$ mAdc)	$V_{CE(sat)}$ $V_{BE(sat)}$	—	-0.6 -1.0	Vdc

1. Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 in².
2. Pulse Test: Pulse Width ≤ 300 μ s; Duty Cycle = 2.0%.

Preferred devices are Motorola recommended choices for future use and best overall value.